
Lecture21: NMOS inverter

Sung-Min Hong (smhong@gist.ac.kr)

Semiconductor Device Simulation Lab.
School of Electrical Engineering and Computer Science
Gwangju Institute of Science and Technology

Why digital?

- You know the answer.
 - And you know what it actually is. (Binary)
- Today, we will consider the following questions:
 - How can we treat the arithmetic operations (Addition, subtraction, multiplication, ...)
 - What is the elemental operation?
 - Then, what are the essential circuits to build such a system?
 - (It will be a short review on Digital Design.)
- Inverter and NAND gates

Addition

- Once you can add two numbers, x and y , you can do
 - Addition, $x + y$ (of course)
 - Subtraction, $x - y = x + (-y)$
 - A simple example) 4-digit binary numbers, $a = 0110$ and $b = 0011$.
 - The 1's complement of b is 1100.
 - The 2's complement of b is 1101.
 - Sum of 0110 and 1101 is 10011.
 - Discarding the end carry gives us the correct answer, 0011.
 - Multiplication, $x \times y$

Even in addition,

- You can recognize that
 - Addition of two 1-bit binary numbers is the core operation!
 - There are only four possible cases!

$$0 + 0 = 0$$

$$0 + 1 = 1$$

$$1 + 0 = 1$$

$$1 + 1 = 10 \leftarrow \text{Carry}$$

Inclusion of carry-bit

- We introduce a separate bit for representing the carry.

- Carry-bit & sum-bit

$$0 + 0 = 00$$

$$0 + 1 = 01$$

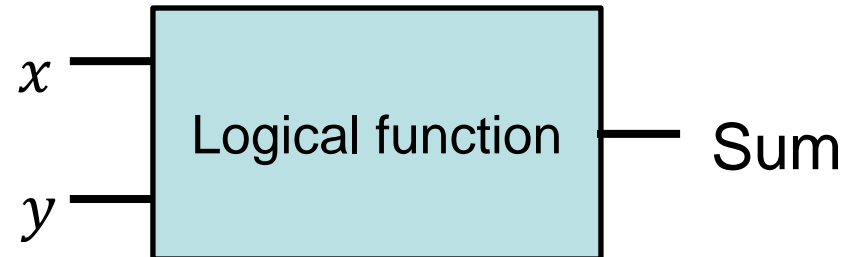
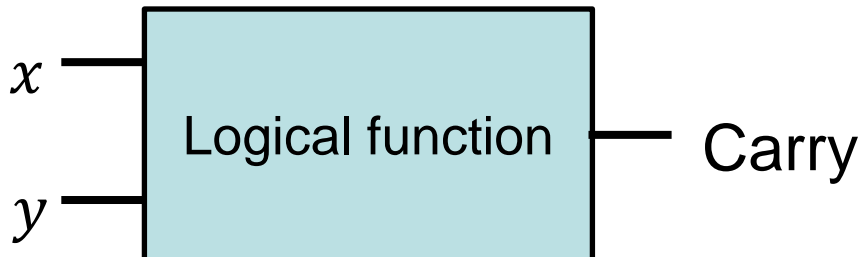
$$1 + 0 = 01$$

$$1 + 1 = 10$$

Carry

Sum

- Treat them separately!



Relation btw x , y , and sum

- Concentrate on the sum-bit.
 - A table can be made.
 - It is called a **truth table**.

x	y	sum
0	0	0
0	1	1
1	0	1
1	1	0

- Yes, it is the exclusive OR, $x \text{ XOR } y$.

Relation btw x , y , and carry

- Concentrate on the carry-bit.
 - A table can be made, again.

x	y	carry
0	0	0
0	1	0
1	0	0
1	1	1

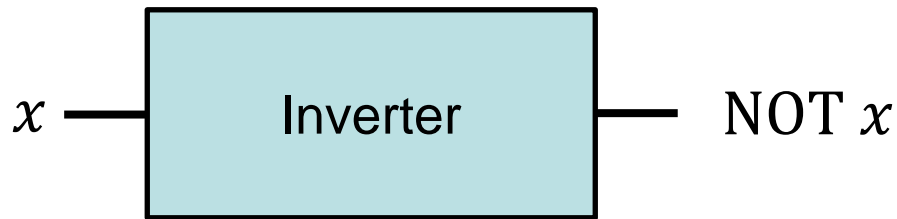
- Yes, it is the AND operation, x AND y

After all,

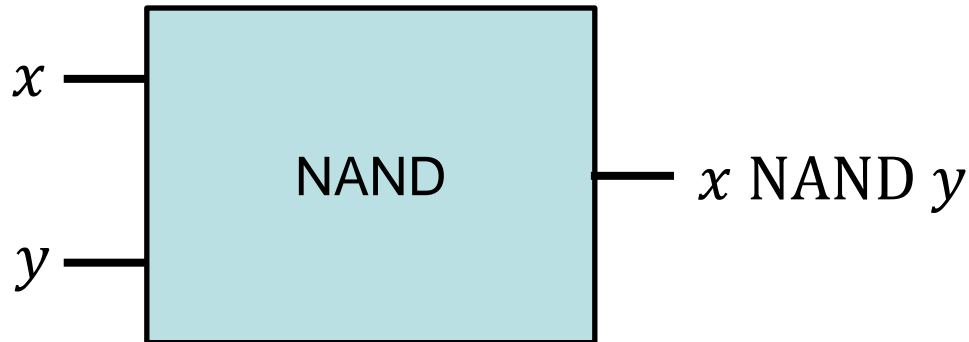
- As much as we have AND, OR, and NOT gates, we can implement any Boolean function.
 - For example,
$$x \text{ XOR } y = (x \text{ AND } (\text{NOT } y)) \text{ OR } ((\text{NOT } x) \text{ AND } y)$$
 - With NAND, NOR, and NOT gates, we can, too.

Inverter and NAND

- NOR can be implemented similarly.



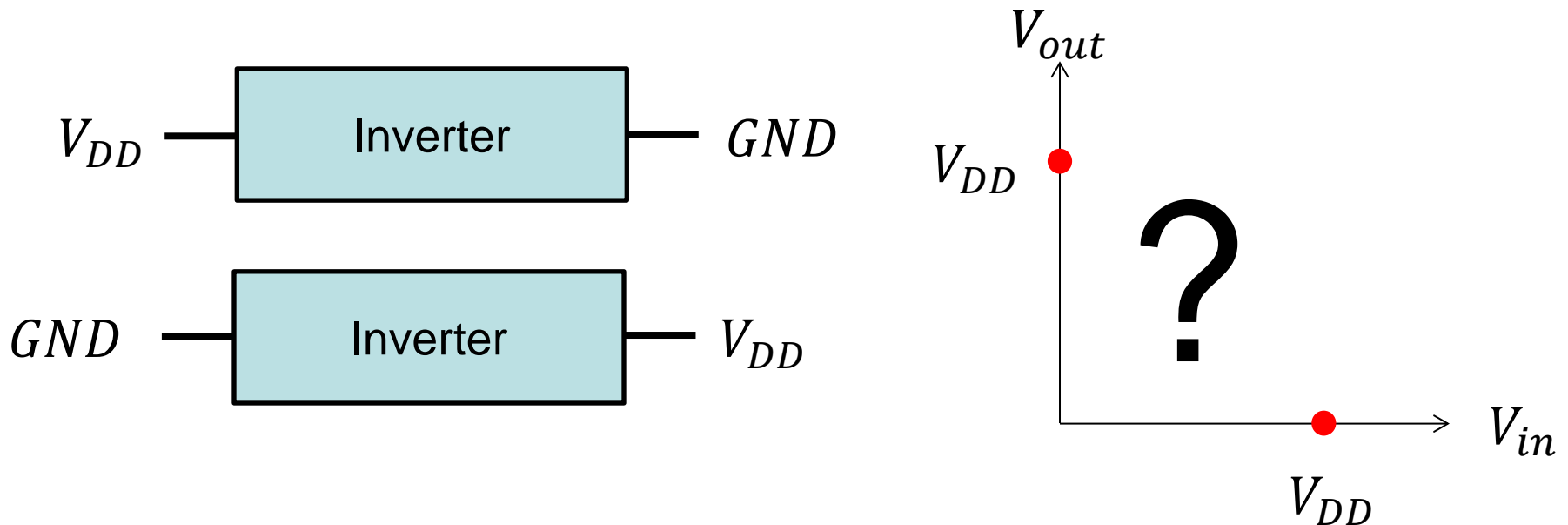
x	NOT
0	1
1	0



x	y	NAND
0	0	1
0	1	1
1	0	1
1	1	0

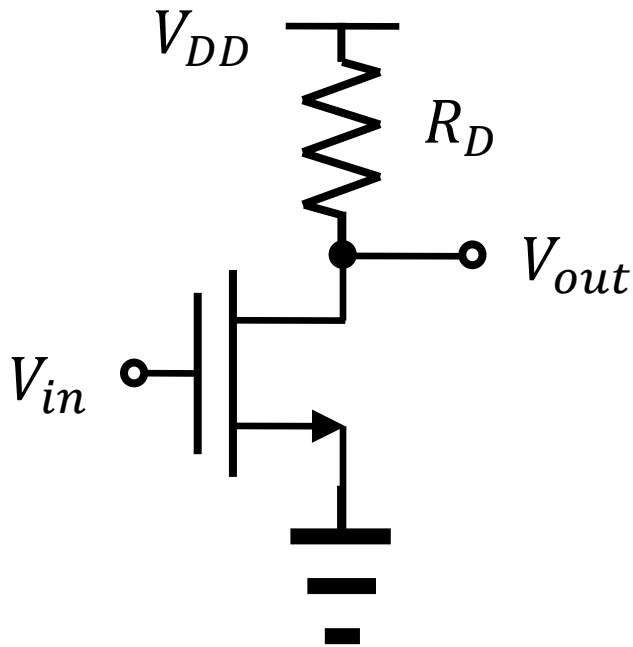
In circuit,

- How can we represent 0 and 1?
 - V_{DD} is assigned to the logical value, 1.
 - GND is assigned to the logical value, 0.



NMOS inverter

- How can we have an output, 0?
 - Only when the input is high. *You have seen it before!*



Vin	Vout
0	1
1	0

Voltage transfer

- When $V_{in} < V_{TH}$, trivially, $V_{out} = V_{DD}$.
- When V_{in} is slightly larger than V_{TH} , the NMOSFET is in the saturation region.

$$V_{out} = V_{DD} - I_D R_D$$
$$V_{out} = V_{DD} - \frac{1}{2} \mu_n C_{ox} \frac{W}{L} R_D (V_{in} - V_{TH})^2$$

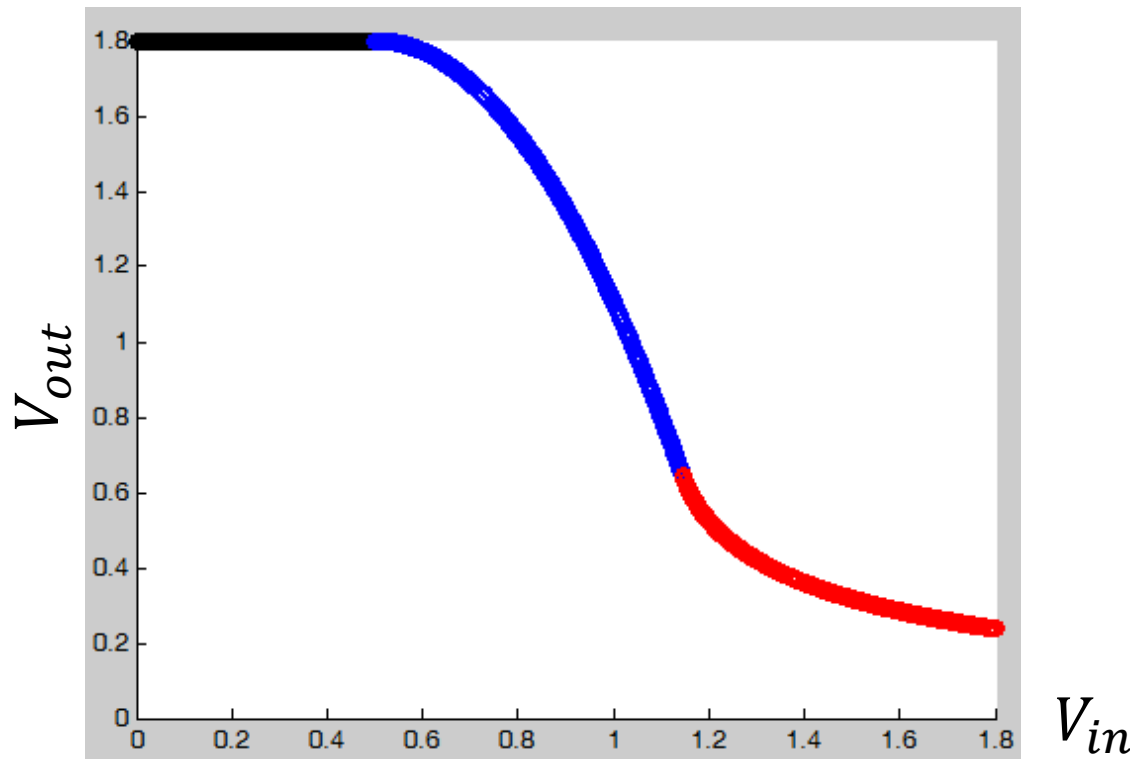
- When V_{in} is further increased, the NMOSFET is in the triode region.

$$V_{out} = V_{DD} - \frac{1}{2} \mu_n C_{ox} \frac{W}{L} R_D [2(V_{in} - V_{TH})V_{out} - V_{out}^2]$$

Draw it! (1/2)

- Parameters in Example 17. 14 (Razavi) w/o modification.

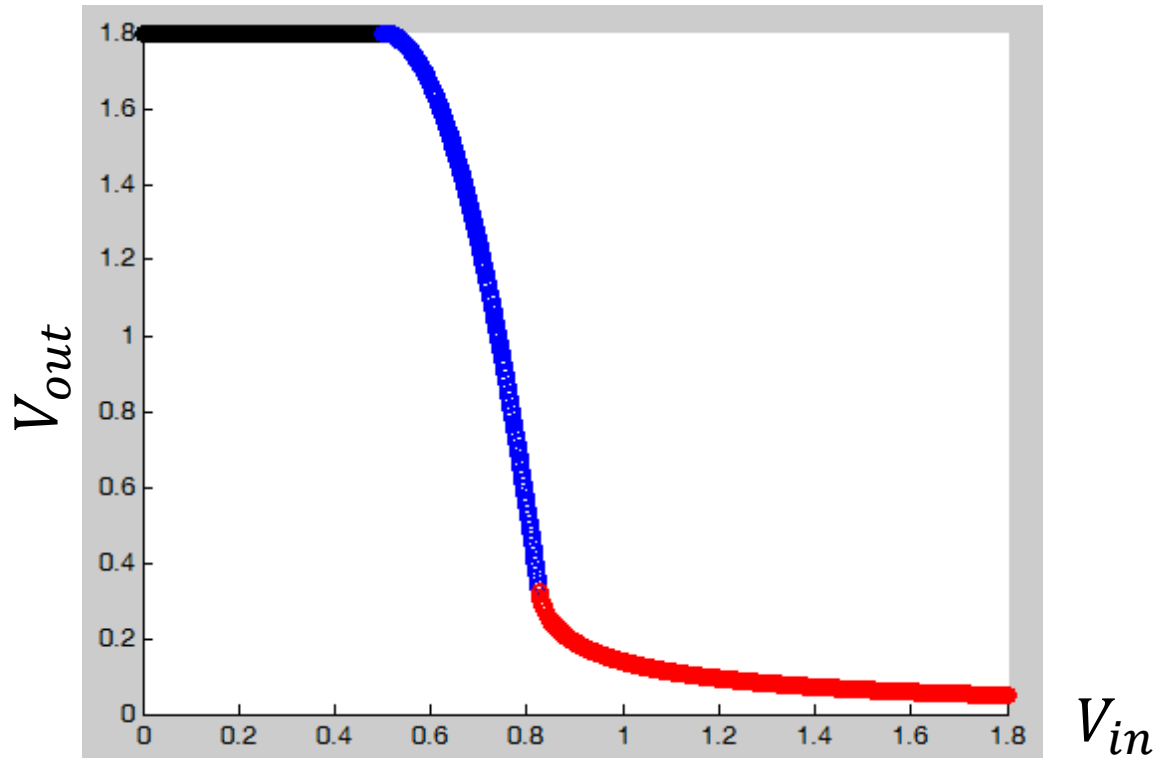
$$\mu_n C_{ox} = 100 \mu\text{A}/\text{V}^2, V_{TH} = 0.5 \text{ V}, \frac{W}{L} = \frac{10}{0.18}, R_D = 1\text{k}\Omega \text{ and } V_{DD} = 1.8 \text{ V}$$



Draw it! (2/2)

- With a wider NMOSFET

$$\mu_n C_{ox} = 100 \mu\text{A}/\text{V}^2, V_{TH} = 0.5 \text{ V}, \frac{W}{L} = \frac{50}{0.18}, R_D = 1\text{k}\Omega \text{ and } V_{DD} = 1.8 \text{ V}$$



Homework#9

- Due: 09:00, **May 27 (Mon)**
- Solve the following problems of the final exam in 2018.
 - P9
 - P10
 - P11
 - P12
 - P13
 - P14